

IN THE SPECIFICATION:

At page 9, third new paragraph, replace that paragraph with the following twice-amended paragraph:

B1  
In the inventive process, the layer patterning characteristic can be enhanced, and the contact resistance between the insulating layer 200 and the lower electrode 202a can be decreased by forming the first wire line 202b and the lower electrode 202a in a particularly preferred manner. In this embodiment, the first wire line 202b and the lower electrode 202a are formed and etched by using a photoresist pattern (not shown) as a mask to define both a capacitor formation part and a wire line formation part. The first wire line 202b and the lower electrode 202a preferably are formed by successively depositing a metal barrier layer (not shown), the first conductive layer and an anti-reflection layer (not shown) on the insulating substrate 200. The metal barrier layer and/or the anti-reflection layer can be: (i) a single-level structure containing a material selected from Ti, Ta, Mo, TiN, TiW, TaN, and MoN and/or (ii) a multi-level structure containing materials selected from W-N, W-Si-N, Ta-Si-N, W-B-N, and Ti-Si-N.

The changes in the previous paragraph are indicated by brackets for deletions and underlining for insertions.

In the inventive process, the layer patterning characteristic can be enhanced, and the contact resistance between the insulating layer 200 and the lower electrode 202a can be decreased by forming the first wire line 202b and the lower electrode 202a in a particularly preferred manner. In this embodiment, the first wire line 202b and the lower electrode 202a are formed and etched by using a photoresist pattern (not shown) as a mask to define both a capacitor formation part and a wire line formation part. The first wire line 202b and the lower electrode 202a preferably are formed by successively depositing a metal barrier layer (not shown), the first conductive layer and an anti-reflection layer (not shown) on the insulating substrate 200. The metal barrier layer and/or the anti-reflection layer can be: (i) a single-level structure containing a material selected from Ti, Ta, Mo, TiN, TiW, TaN, and MoN[;] and/or (ii) a multi-level structure containing materials selected from W-N, W-Si-N, Ta-Si-N, W-B-N, and Ti-Si-N[; and/or (iii) combination layers of (i) and (ii)].